

In the Claims

Please amend the claims as follows:

Claims 1-20 (canceled).

21. (Currently amended) A molecular electronic device or circuit comprising:
a substrate comprising a surface on which is located a first electrode pattern having an interior surface;
a second electrode pattern having an interior surface wherein said second electrode pattern overlaps said first electrode pattern to form a plurality of electrode intersections located between the interior surfaces of said first and second electrode patterns;
a layer of electrically conductive protective material that is located only on the interior surface of said second electrode pattern; and
a layer of molecules having an electrical characteristic located adjacent to said layer of electrically conductive material wherein said one or more electrode intersections comprise said molecules and said electrically conductive protective material sandwiched between said first and second electrode patterns.

22. (Original) A molecular electronic device according to claim 21 wherein said molecules have the electrical characteristic of bistable switching.

23. (Original) A molecular electronic device according to claim 21 wherein said first and second electrode patterns have nanometer scale dimensions.

24. (Canceled)

25. (Previously presented) A molecular electronic device or circuit in accordance with claim 21 wherein said substrate comprises a material selected from the group consisting of an organic polymer, silicon, germanium, gallium arsenide, silicon dioxide, or sapphire.

26. (Previously presented) A molecular electronic device or circuit in accordance with claim 21 wherein said molecular layer comprises bistable switching molecules selected from the group consisting of rotoxanes, catenanes, and pseudorotaxanes.

27. (Previously presented) A molecular electronic device or circuit in accordance with claim 21 wherein said electrically conductive material which is used to form said protective layer is selected from the group of metals consisting of titanium and chromium.

28. (Previously presented) A molecular electronic device or circuit in accordance with claim 21 wherein said molecular layer is formed as a self-assembled molecular monolayer film or is formed as a Langmuir-Blodgett molecular monolayer or multilayer film or is deposited via vapor sublimation or vapor deposition.

29. (Previously presented) A molecular electronic device or circuit in accordance with claim 21 wherein said first electrode pattern is made from a material selected from the group consisting of aluminum, gold, silver, cobalt, iron, nickel, tin, copper, platinum, palladium and alloys thereof, and silicon, polysilicon, amorphous silicon, gallium arsenide and doped polymers.

30. (Previously presented) A molecular electronic device or circuit in accordance with claim 21 wherein second electrode pattern is made from a material selected from the group consisting of aluminum, gold, silver, cobalt, iron, nickel, tin, copper, platinum, palladium and alloys thereof, and silicon, polysilicon, amorphous silicon, gallium arsenide and doped polymers.